

APPENDIX

Changes to Claims:

Claims 15 and 16 are added.

The following are marked-up versions of the amended claims:

1. (Amended) A semiconductor device, comprising:

~~a silicon substrate and~~

~~a metal-oxide-semiconductor field-effect transistor formed on said silicon substrate,~~

~~wherein a gate electrode of said transistor comprises a germanium film that includes:~~

~~a gate insulation film and a gate electrode on the gate insulation film, the gate electrode including a germanium film on the gate insulation film.~~

7. (Amended) A semiconductor device, comprising:

~~an n-channel metal-oxide-semiconductor field-effect transistor; and~~

~~a p-channel metal-oxide-semiconductor field-effect transistor,~~

~~wherein a gate electrode of each of said transistors comprises any one of a single crystalline germanium film, a polycrystalline germanium film or an amorphous germanium film in which p-type impurities are doped at least one of the n-channel metal-oxide-semiconductor field-effect transistor and the p-channel metal-oxide-semiconductor field-effect transistor including:~~

~~a gate insulation film and a gate electrode on the gate insulation film, the gate electrode including a germanium film on the gate insulation film.~~